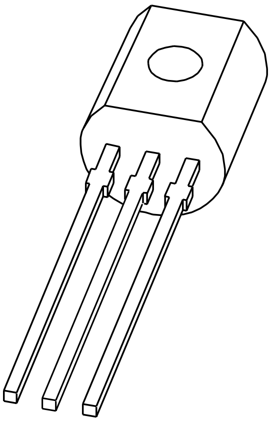
DATA SHEET



BC546; BC547

NPN general purpose transistors

Product specification
Supersedes data of 1997 Mar 04

1999 Apr 15

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complements: BC556 and BC557.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector

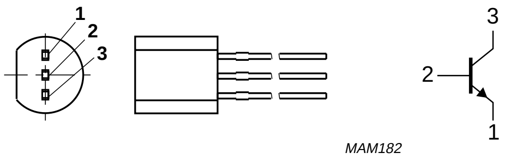


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC546		–	80	V
	BC547		–	50	V
V_{CEO}	collector-emitter voltage	open base			
	BC546		–	65	V
	BC547		–	45	V
V_{EBO}	emitter-base voltage	open collector			
	BC546		–	6	V
	BC547		–	6	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	0.25	K/mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

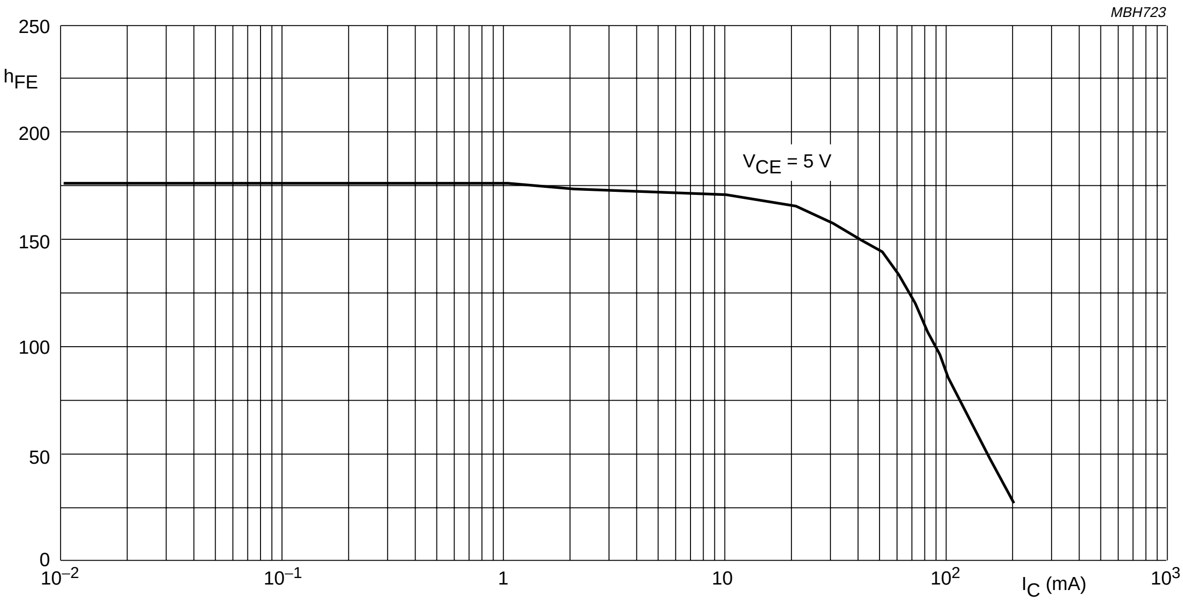
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; V_{CB} = 30 V	–	–	15	nA
		$I_E = 0$; V_{CB} = 30 V; T_j = 150 °C	–	–	5	µA
I_{EBO}	emitter cut-off current	$I_C = 0$; V_{EB} = 5 V	–	–	100	nA
h_{FE}	DC current gain	I_C = 10 µA; V_{CE} = 5 V; see Figs 2, 3 and 4				
	BC546A		–	90	–	
	BC546B; BC547B		–	150	–	
	BC547C		–	270	–	
	DC current gain	I_C = 2 mA; V_{CE} = 5 V; see Figs 2, 3 and 4				
	BC546A		110	180	220	
	BC546B; BC547B		200	290	450	
	BC547C		420	520	800	
	BC547		110	–	800	
	BC546		110	–	450	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA	–	90	250	mV
		I_C = 100 mA; I_B = 5 mA	–	200	600	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; note 1	–	700	–	mV
		I_C = 100 mA; I_B = 5 mA; note 1	–	900	–	mV
V_{BE}	base-emitter voltage	I_C = 2 mA; V_{CE} = 5 V; note 2	580	660	700	mV
		I_C = 10 mA; V_{CE} = 5 V	–	–	770	mV
C_c	collector capacitance	$I_E = i_e = 0$; V_{CB} = 10 V; f = 1 MHz	–	1.5	–	pF
C_e	emitter capacitance	$I_C = i_c = 0$; V_{EB} = 0.5 V; f = 1 MHz	–	11	–	pF
f_T	transition frequency	I_C = 10mA; V_{CE} = 5 V; f = 100 MHz	100	–	–	MHz
F	noise figure	I_C = 200 µA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	2	10	dB

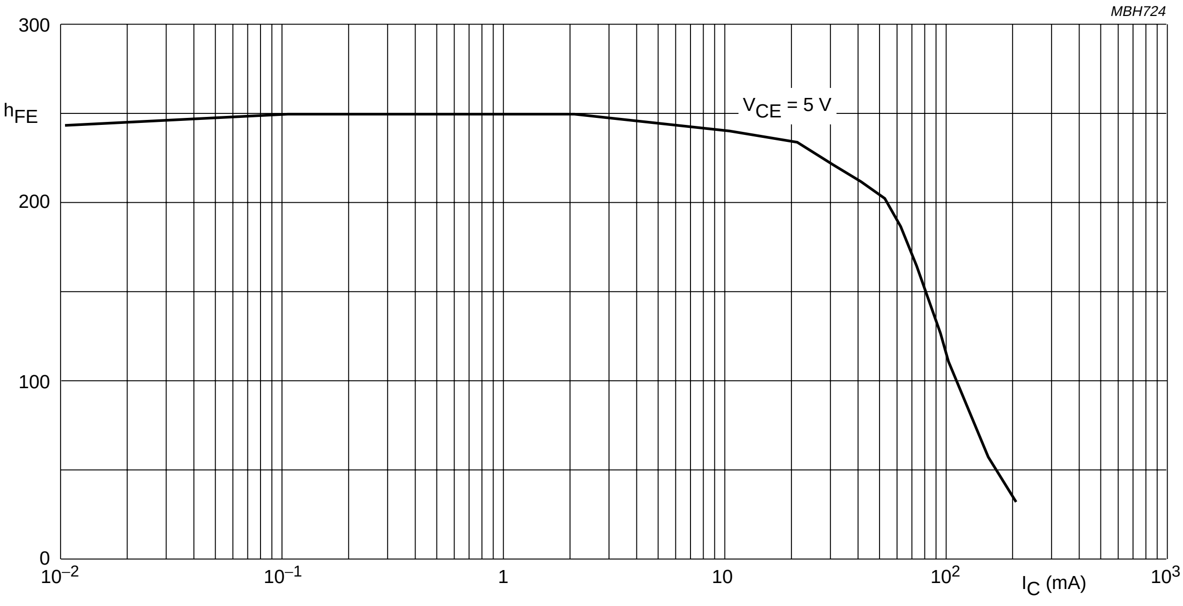
Notes

1. V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
2. V_{BE} decreases by about 2 mV/K with increasing temperature.



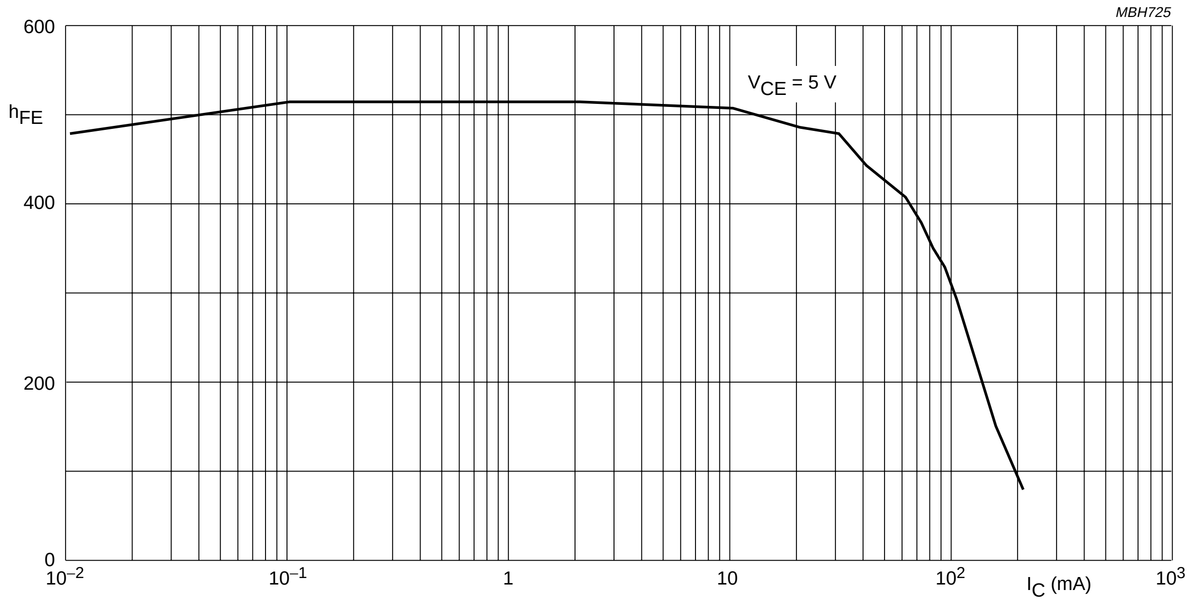
BC546A.

Fig.2 DC current gain; typical values.



BC546B; BC547B.

Fig.3 DC current gain; typical values.

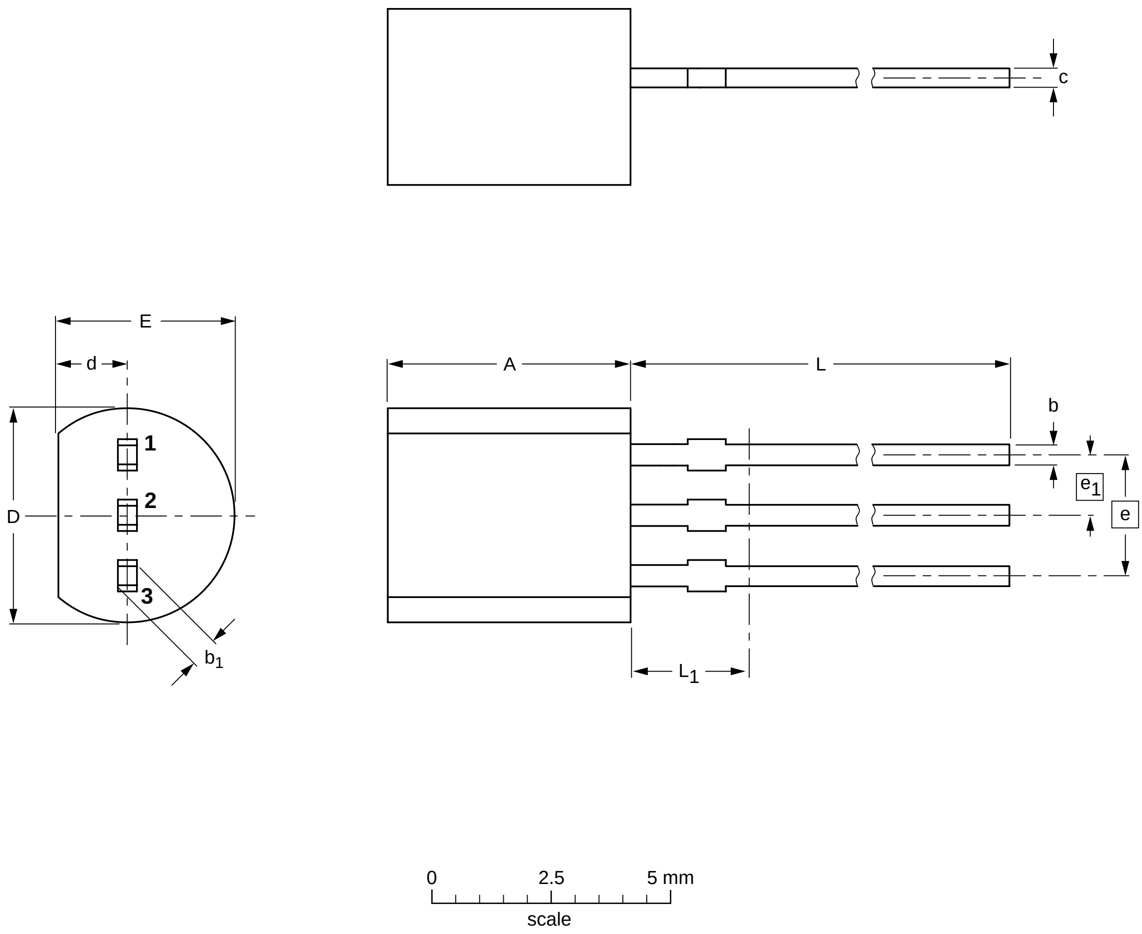


BC547C.

Fig.4 DC current gain; typical values.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**

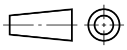


DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	$L_1^{(1)}$
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54		TO-92	SC-43			97-02-28